ABSTRACT

An object of the present invention is to provide a nitride semiconductor product which causes no time-dependent deterioration in reverse withstand voltage and maintains a satisfactory initial reverse withstand voltage.

The inventive nitride semiconductor product comprises an n-type layer, a light-emitting layer, and a p-type layer which are formed of a nitride semiconductor and sequentially stacked on a substrate in the above order,

the light-emitting layer having a quantum well structure in which a well layer is sandwiched by barrier layers having band gaps wider than the band gap of the well layer,

wherein each barrier layer comprises a barrier sublayer C which has been grown at a temperature higher than a growth temperature of the well layer, and a barrier sublayer E which has been grown at a temperature lower than a growth temperature of the barrier sublayer C, and the barrier sublayer C is disposed closer to the substrate with respect to the barrier sublayer E.